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Vishay Siliconix

Automotive N-Channel 200 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	200			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.035			
I _D (A)	60			
Configuration	Single			
Package	TO-263			



FEATURES

- TrenchFET® power MOSFET
- Package with low thermal resistance
- AEC-Q101 qualified d
- 100 % R_a and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

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G o —	
N-Channel MOSFET	d s

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	200	V	
Gate-Source Voltage		V_{GS}	± 20	V	
Continuous Drain Current	T _C = 25 °C	1	60		
Continuous Drain Current	T _C = 125 °C	l _D	35		
Continuous Source Current (Diode Conduction	Is	120	Α		
Pulsed Drain Current ^b	I _{DM}	100			
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	26		
Single Pulse Avalanche Energy	L = U.T IIIH	E _{AS}	33	mJ	
Maximum Power Dissipation ^b	T _C = 25 °C	D	375	W	
waxiinum rowei Dissipation -	T _C = 125 °C	P_{D}	125	vV	
Operating Junction and Storage Temperature	T_J , T_{stg}	-55 to +175	°C		

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-Ambient	PCB Mount c	R _{thJA}	40	°C/W		
Junction-to-Case (Drain)		R _{thJC}	0.4	C/VV		

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR4 material).
- d. Parametric verification ongoing.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static						I.	ı	
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} :	= 0 V, I _D = 250 μA	200	-	-	V	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μA	2.5	3.0	3.5	V	
Gate-Source Leakage	I _{GSS}	V _{DS} =	0 V, V _{GS} = ± 20 V	-	-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = 200 V	-	-	1	μА	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 200 V, T _J = 125 °C	-	-	75	μΑ	
		V _{GS} = 0 V	V _{DS} = 200 V, T _J = 175 °C	-	-	2	mA	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	60	-	-	Α	
		V _{GS} = 10 V	I _D = 20 A	-	0.028	0.035	Ω	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 20 A, T _J = 125 °C	-	-	0.074		
	, ,	V _{GS} = 10 V	I _D = 20 A, T _J = 175 °C	-	-	0.098		
Forward Transconductance b	9 _{fs}	V _{DS} = 15 V, I _D = 20 A		-	67	=.	S	
Dynamic ^b								
Input Capacitance	C _{iss}			-	4655	5850		
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{GS} = 0 \text{ V}$ $V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$		410	550	рF	
Reverse Transfer Capacitance	C _{rss}			-	195	250		
Total Gate Charge ^c	Qg			-	90	135		
Gate-Source Charge ^c	Q _{gs}	$V_{GS} = 10 \text{ V}$	$V_{DS} = 100 \text{ V}, I_{D} = 9 \text{ A}$	-	16	-	nC	
Gate-Drain Charge ^c	Q_{gd}			-	29	=.		
Gate Resistance	R_g		f = 1 MHz	0.3	0.8	1.5	Ω	
Turn-On Delay Time ^c	t _{d(on)}		V _{DD} = 100 V, R _I = 11.1 Ω		20	30		
Rise Time ^c	t _r				40	60	ns	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 9 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		-	35	53		
Fall Time ^c	t _f			-	20	30		
Source-Drain Diode Ratings and Chara	cteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	100	Α	
Forward Voltage	V _{SD}	I _F = 30 A, V _{GS} = 0 V		-	0.8	1.5	V	

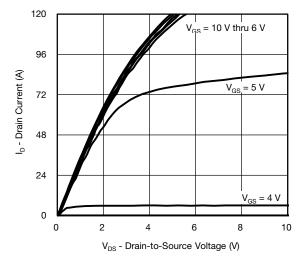
Notes

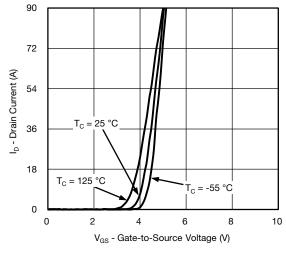
- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

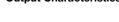


TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

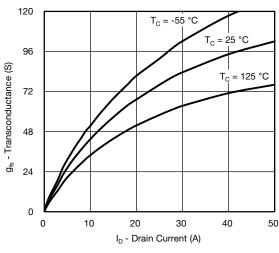


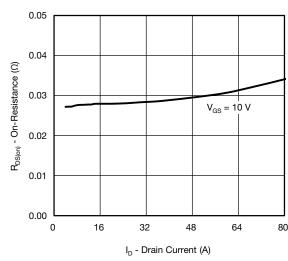


Output Characteristics



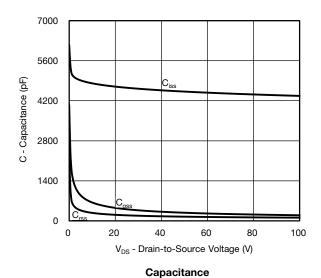


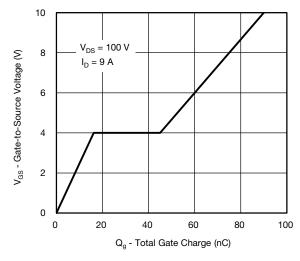




Transconductance

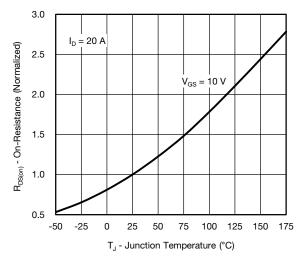
On-Resistance vs. Drain Current

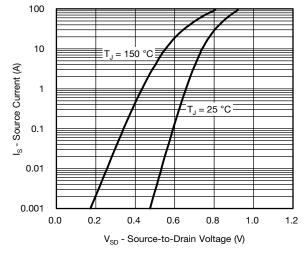






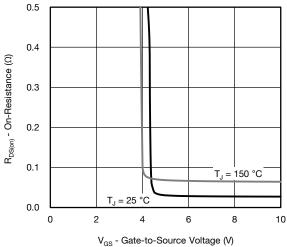
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



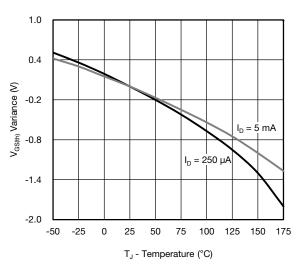


On-Resistance vs. Junction Temperature



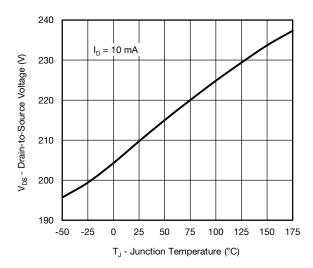


Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

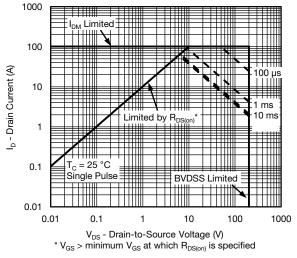




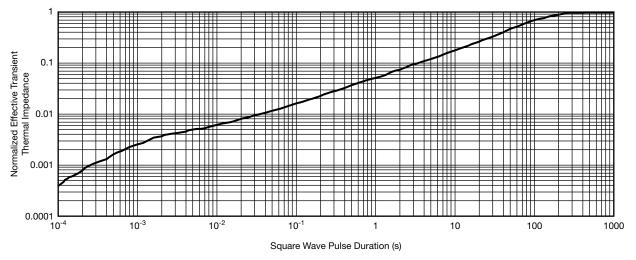
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



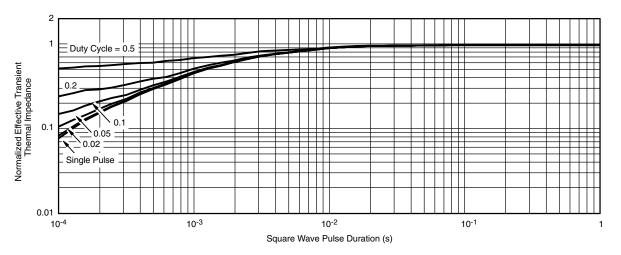
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

The characteristics shown in the two graphs

S15-1874-Rev. B, 10-Aug-15

- Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction to Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62744



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REVISION HISTORY ^a				
REVISION	DATE	DESCRIPTION OF CHANGE		
В	04-Aug-15	Revised R _g minimum limit		

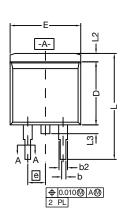
Note

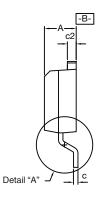
a. As of April 2014

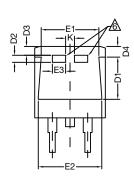




TO-263 (D²PAK): 3-LEAD

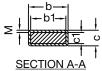








DETAIL A (ROTATED 90°)



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ı	WHITTEN S	1	1

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6 This feature is for thick lead.

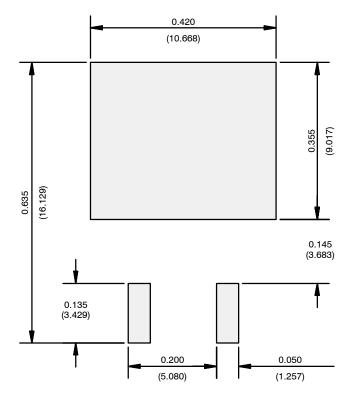
		INC	HES	MILLIMETERS		
	DIM.	MIN.	MAX.	MIN.	MAX.	
	Α	0.160	0.190	4.064	4.826	
	b	0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457	
	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1	0.220	0.240	5.588	6.096	
	D2	0.038	0.042	0.965	1.067	
	D3	0.045	0.055	1.143	1.397	
	D4	0.044	0.052	1.118	1.321	
	E	0.380	0.410	9.652	10.414	
	E1	0.245	-	6.223	-	
	E2	0.355	0.375	9.017	9.525	
	E3	0.072	0.078	1.829	1.981	
	е	0.100	BSC	2.54 BSC		
	K	0.045	0.055	1.143	1.397	
L		0.575	0.625	14.605	15.875	
L1		0.090	0.110	2.286	2.794	
L2		0.040	0.055	1.016	1.397	
	L3	0.050	0.070	1.270	1.778	
L4		0.010 BSC		0.254 BSC		
	М	-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13						

DWG: 5843





RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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